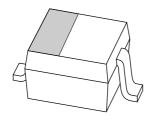
DISCRETE SEMICONDUCTORS

DATA SHEET



BAP1321-03 Silicon PIN diode

Product specification
Supersedes data of 2001 May 11

2004 Feb 17





Silicon PIN diode BAP1321-03

FEATURES

- High voltage, current controlled
- RF resistor for RF attenuators and switches
- Low diode capacitance
- Low diode forward resistance
- · Very low series inductance
- For applications up to 3 GHz.

APPLICATIONS

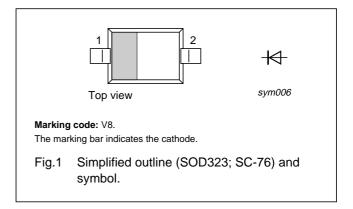
• RF attenuators and switches.

DESCRIPTION

Planar PIN diode in a SOD323 (SC-76) ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



ORDERING INFORMATION

TYPE		PACKAGE	
NUMBER	NAME	DESCRIPTION	VERSION
BAP1321-03	_	plastic surface mounted package; 2 leads	SOD323

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		_	60	V
I _F	continuous forward current		_	100	mA
P _{tot}	total power dissipation	T _s ≤ 90 °C	_	500	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C

Silicon PIN diode BAP1321-03

CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	forward voltage	I _F = 50 mA	0.95	1.1	V
I _R	reverse leakage current	V _R = 60 V	_	100	nA
C _d	diode capacitance	V _R = 0; f = 1 MHz	0.4	-	pF
		V _R = 1 V; f = 1 MHz	0.35	0.45	pF
		V _R = 20 V; f = 1 MHz	0.25	0.32	pF
r _D	diode forward resistance	f = 100 MHz; note 1			
		I _F = 0.5 mA	3.4	5.0	Ω
		I _F = 1 mA	2.4	3.6	Ω
		I _F = 10 mA	1.2	1.8	Ω
		I _F = 100 mA	0.85	1.3	Ω
S ₂₁ ²	isolation	V _R = 0; f = 900 MHz	16.6	-	dB
		V _R = 0; f = 1800 MHz	11.6	Ī-	dB
		V _R = 0; f = 2450 MHz	9.2	-	dB
S ₂₁ ²	insertion loss	I _F = 0.5 mA; f = 900 MHz	0.26	Ī-	dB
		I _F = 0.5 mA; f = 1800 MHz	0.35	Ī-	dB
		I _F = 0.5 mA; f = 2450 MHz	0.44	-	dB
S ₂₁ ²	insertion loss	I _F = 1 mA; f = 900 MHz	0.20	-	dB
		I _F = 1 mA; f = 1800 MHz	0.29	Ī-	dB
		I _F = 1 mA; f = 2450 MHz	0.38	Ī-	dB
S ₂₁ ²	insertion loss	I _F = 10 mA; f = 900 MHz	0.13	Ī-	dB
		I _F = 10 mA; f = 1800 MHz	0.22	_	dB
		I _F = 10 mA; f = 2450 MHz	0.32	-	dB
S ₂₁ ²	insertion loss	I _F = 100 mA; f = 900 MHz	0.10	Ī-	dB
		I _F = 100 mA; f = 1800 MHz	0.20	-	dB
		I _F = 100 mA; f = 2450 MHz	0.29	_	dB
τ∟	charge carrier life time	when switched from I_F = 10 mA to I_R = 6 mA; R_L = 100 Ω ; measured at I_R = 3 mA	0.5	_	μs
L _S	series inductance	I _F = 100 mA; f = 100 MHz	1.5	-	nH

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th(j-s)}	thermal resistance from junction to soldering point	120	K/W

^{1.} Guaranteed on AQL basis: inspection level S4, AQL 1.0.

Silicon PIN diode BAP1321-03

GRAPHICAL DATA

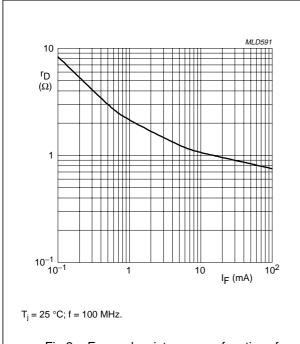
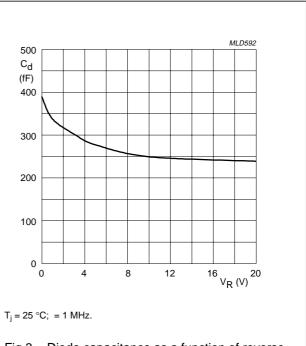
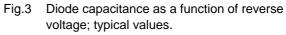
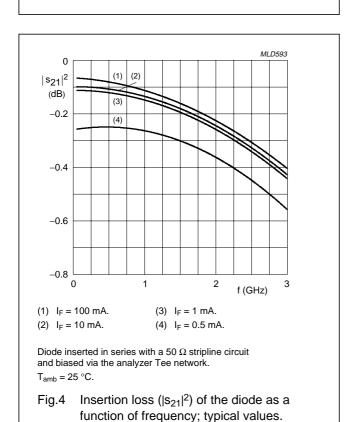
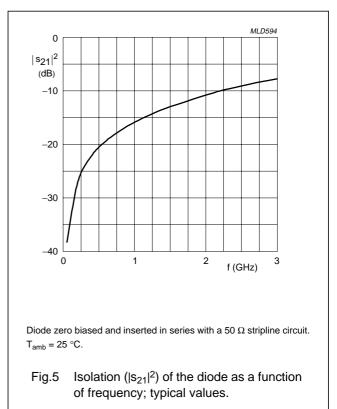


Fig.2 Forward resistance as a function of forward current; typical values.









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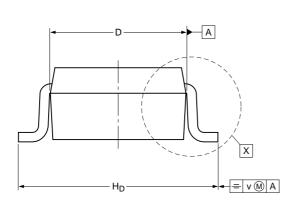
Silicon PIN diode

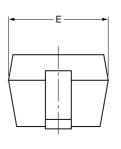
BAP1321-03

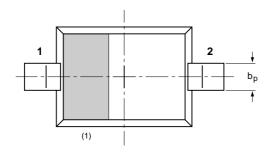
PACKAGE OUTLINE

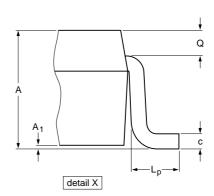
Plastic surface mounted package; 2 leads

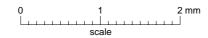
SOD323











DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁ max	bp	С	D	E	H _D	Lp	Q	v
mm	1.1 0.8	0.05	0.40 0.25	0.25 0.10	1.8 1.6	1.35 1.15	2.7 2.3	0.45 0.15		0.2

Note

1. The marking bar indicates the cathode

OUTLINE	NE REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOD323			SC-76			99-09-13 03-12-17

Silicon PIN diode BAP1321-03

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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